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研究方向 ·集成电路制造
·计算光刻（结合机器学习、基因算法）

中国科学院大学博士、博士后。现任浙江大学微纳电子学院特聘研究员。近5年一直致力于相变材料的开发、优化、以及相变机理研究。目前从事55 nm 低功耗CMOS成套工艺开发。迄今，以第一作者或通讯作者在ACS Applied Materials & Interfaces，Nanoscale，Applied Physics Letters，Scripta Materialia，Journal of Alloys and Compounds和Scientific Reports等国际著名学术期刊发表论文近20余篇，申请专利10余项，主持国家自然基金1项，浙江省自然基金1项，国家重点实验室开放课题1项。

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1. **K. Ren**, M. Xia, S. Zhu, G. Wang, T. Xin, S. Lv, Z. Song, Crystal-Like Glassy Structure in Sc-Doped BiSbTe Ensuring Excellent Speed and Power Efficiency in Phase Change Memory, **ACS Appl. Mater. Interfaces**, 2020, 12,16601.

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1. Bi0.5Sb1.5Te3基相变存储器低压低功耗性能优化及相变机理研究 国家自然科学基金青年项目
2. O-Ti-Sb-Te 相变材料以及在突触器件中的应用 浙江省自然科学基金青年项目
3. C粘附层增强相变存储器界面高温稳定性的研究 国家重点实验室开放课题